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Characteristic		Symbol	Value	Unit
Drain-Source Voltage		V <sub>DSS</sub>	100	V
Gate-Source Voltage		$V_{GSS}$	±20	V
Continuous Drain Current (Note 5) V <sub>GS</sub> = 10V	$T_A = +25$ °C $T_A = +70$ °C	I <sub>D</sub>	2.3 1.8	А
	$T_C = +25$ °C $T_C = +70$ °C	I <sub>D</sub>	6.2 4.9	А
Maximum Continuous Body Diode Forward Current (Note 5)		Is	1.5	Α
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)		I <sub>DM</sub>	8	Α

## Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	TA = +25°C	- P <sub>D</sub>	1.8	W
	TA = +70°C		1.1	
Thermal Resistance, Junction to Ambient (Note 5)		$R_{\theta JA}$	69	°C/W
Total Power Dissipation (Note 5)	Tc = +25°C	P <sub>D</sub>	14	W
Thermal Resistance, Junction to Case (Note 5)		$R_{\theta JC}$	8.7	°C/W
Operating and Storage Temperature Range		T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

# **Electrical Characteristics** (@ $T_A = \pm 25$ °C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 6)							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	100	_	_	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	_	_	1	μA	V <sub>DS</sub> = 100V, V <sub>GS</sub> = 0V	
Gate-Source Leakage	I <sub>GSS</sub>	_	_	±100	nA	$V_{GS} = \pm 16V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 6)			•		•		
Gate Threshold Voltage	V <sub>GS(TH)</sub>	1	1.7	2.5	V	$V_{DS} = V_{GS}$ , $I_D = 250\mu A$	
Static Drain-Source On-Resistance		_	155	220	mΩ	$V_{GS} = 10V, I_D = 1.6A$	
Static Dialit-Source Off-Nesistance	R <sub>DS(ON)</sub>	_	190	250		V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 1.3A	
Diode Forward Voltage	V <sub>SD</sub>	_	0.8	1.5	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = 1.1A	
DYNAMIC CHARACTERISTICS (Note 7)			•		•		
Input Capacitance	Ciss	-	401	_		$V_{DS} = 25V, V_{GS} = 0V$ f = 1.0MHz	
Output Capacitance	Coss	_	22	_	pF		
Reverse Transfer Capacitance	C <sub>rss</sub>	_	17	<u> </u>			
Gate Resistance	Rg	_	2.1	_	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$	
Total Gate Charge (V <sub>GS</sub> = 4.5V)	Qg	_	4.1	_		V <sub>DS</sub> = 50V, I <sub>D</sub> = 1.6A	
Total Gate Charge (V <sub>GS</sub> = 10V)	Qg	_	8.3	<u> </u>	nC		
Gate-Source Charge	Q <sub>gs</sub>	_	1.5	_	nc nc		
Gate-Drain Charge	$Q_{gd}$	_	2	_			
Turn-On Delay Time	t <sub>D(ON)</sub>	_	6.8	<u> </u>		$V_{DS} = 50V$ , $V_{GS} = 4.5V$ , $R_G = 6.8\Omega$ , $I_D = 1.0A$	
Turn-On Rise Time	t <sub>R</sub>	_	8.2	_	no		
Turn-Off Delay Time	t <sub>D(OFF)</sub>	_	7.9	_	ns		
Turn-Off Fall Time	t <sub>F</sub>	_	3.6	_			
Reverse Recovery Time	t <sub>RR</sub>	_	17	_	ns	1 4 4 0 - 11/-14 4 4 0 0 0 / 1 - 2	
Reverse Recovery Charge	$Q_{RR}$	_	9.8	<u> </u>	nC	$I_S = 1.1A$ , di/dt =100A/ $\mu$ s	

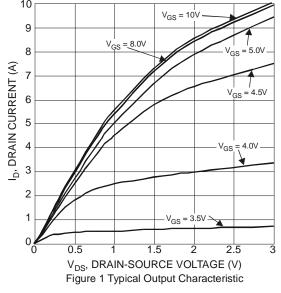
Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal vias to bottom layer 1-inch square copper plate.

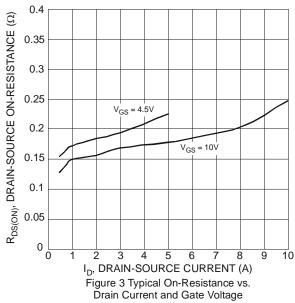
<sup>6.</sup> Short duration pulse test used to minimize self-heating effect.

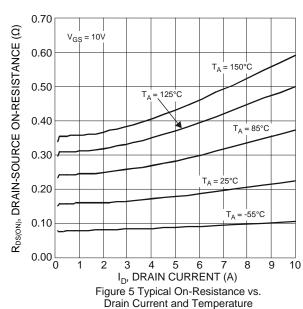
<sup>7.</sup> Guaranteed by design. Not subject to production testing.

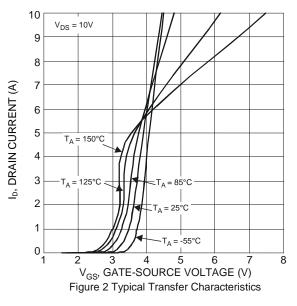


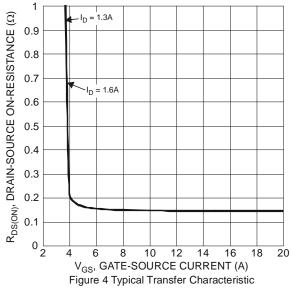












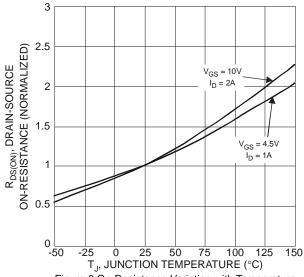
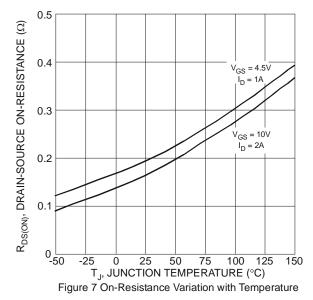


Figure 6 On-Resistance Variation with Temperature

### DMN10H220LE





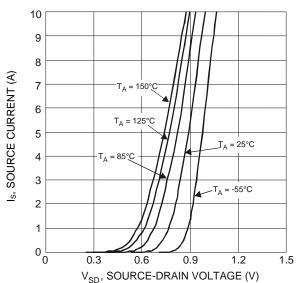
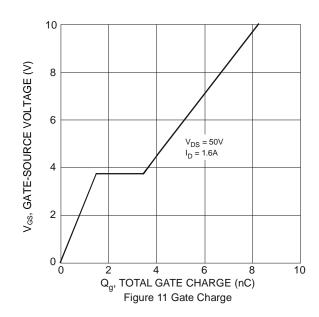


Figure 9 Diode Forward Voltage vs. Current



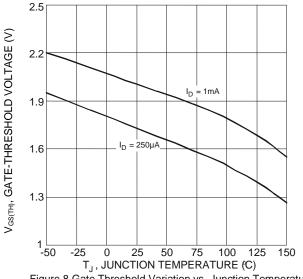
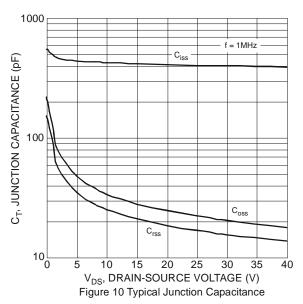
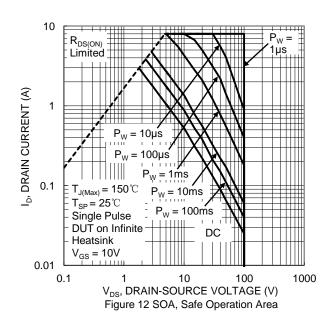
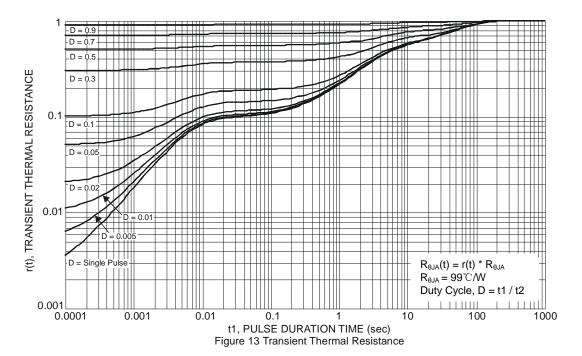


Figure 8 Gate Threshold Variation vs. Junction Temperature







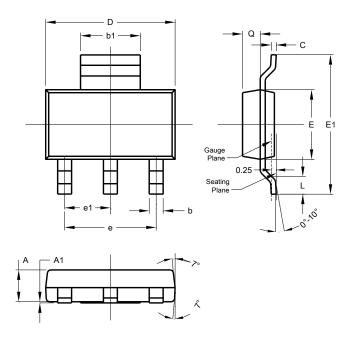




## **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

### **SOT223**

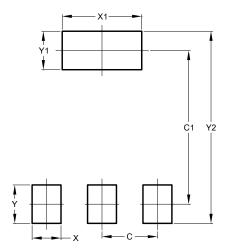


SOT223					
Dim	Min	Max	Тур		
Α	1.55	1.65	1.60		
A1	0.010	0.15	0.05		
b	0.60	0.80	0.70		
b1	2.90	3.10	3.00		
С	0.20	0.30	0.25		
D	6.45	6.55	6.50		
Е	3.45	3.55	3.50		
E1	6.90	7.10	7.00		
е	-	-	4.60		
e1	-	-	2.30		
L	0.85	1.05	0.95		
Q	0.84	0.94	0.89		
All Dimensions in mm					

# Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

### **SOT223**



<b>Dimensions</b>	Value (in mm)
С	2.30
C1	6.40
Х	1.20
X1	3.30
Ý	1.60
Y1	1.60
Y2	8.00



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